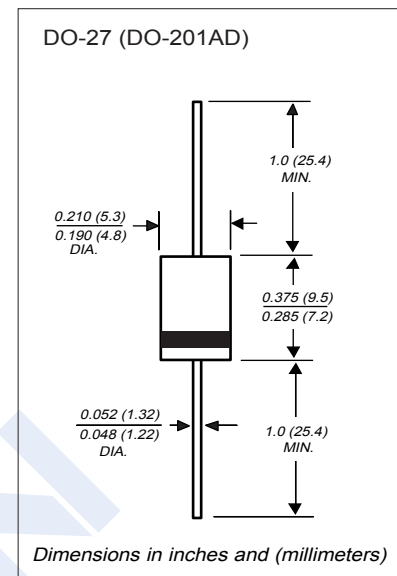


Schottky Diodes

SB320 ~ SB3200

■ Features

- Metal-Semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	SB 320	SB 330	SB 340	SB 350	SB 360	SB 380	SB 3100	SB 3150	SB 3200	Unit	
Repetitive Peak Reverse Voltage	V _{RRM}	20	30	40	50	60	80	100	150	200	V	
RMS Voltage	V _{RMS}	14	21	28	35	42	56	70	105	140		
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	80	100	150	200		
Forward Voltage @ 3A	V _F	0.55		0.7		0.85		0.87		0.9		
Averaged Forward Current	I _{FAV}	3										A
Peak Forward Surge Current @ 8.3ms	I _{FSM}	80										
Maximum DC Reverse Current Ta=25°C	I _R	0.5					0.2					mA
Ta=100°C		10					5					
Typical Junction Capacitance	C _j	180		150		110		100		80	pF	
Thermal Resistance.Junction- to-Ambient	R _{thJA}	60										°C/W
Thermal Resistance.Junction- to-Case	R _{thJC}	15										
Junction Temperature	T _j	125										°C
Storage Temperature	T _{stg}	-55 to 150										

Schottky Diodes

SB320 ~ SB3200

■ Typical Characteristics

FIG. 1-TYPICAL FORWARD CURRENT DERATING CURVE

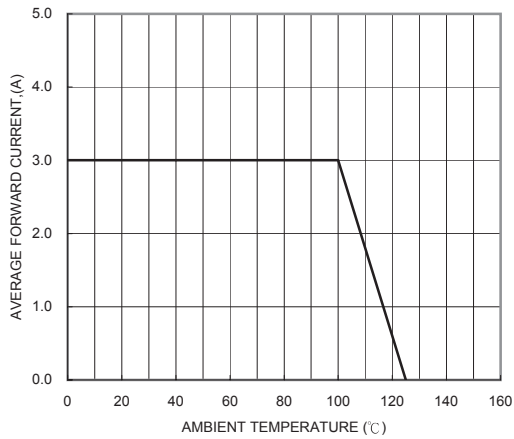


FIG. 2-TYPICAL FORWARD CHARACTERISTICS

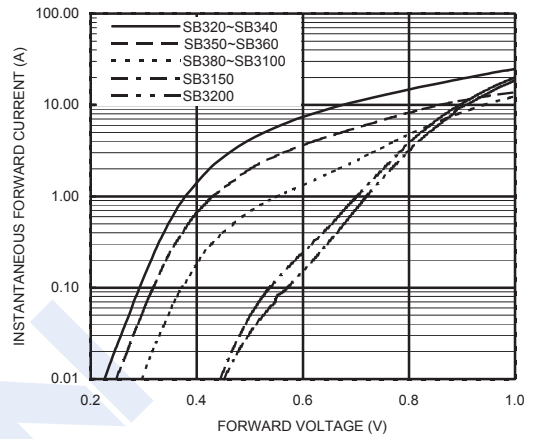


FIG. 3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

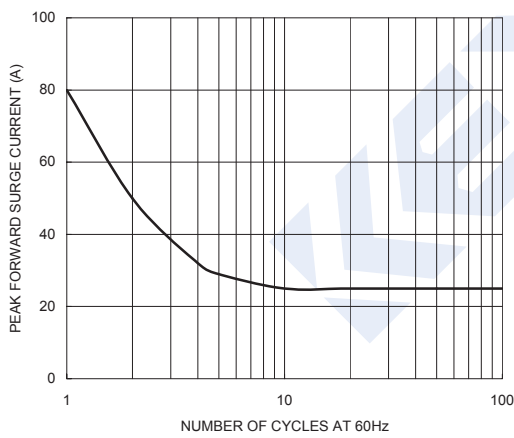


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

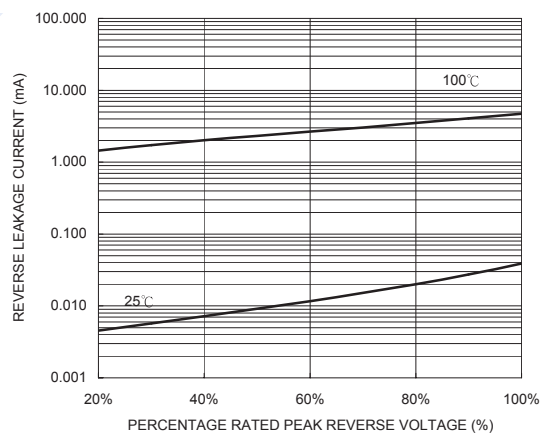


FIG. 5-TYPICAL JUNCTION CAPACITANCE

